

Product Overview

NTHD3101F: P-Channel ChipFET™ Power MOSFET and Schottky Diode -20V - 4.4A 80mΩ

For complete documentation, see the data sheet.

Power MOSFET -20V -4.4A 80mΩ P-Channel ChipFET™4.1 A Schottky Barrier Diode

Features

- Leadless SMD Package Featuring a MOSFET and Schottky Diode
- 40% Smaller than TSOP-6 Package
- Leadless SMD Package Provides Great Thermal Characteristics
- Independent Pinout to each Device to ease Circuit Design
- Trench P-Channel for Low On Resistance
- Ultra Low VF Schottky

Applications

- Li-Ion Battery Charging
- High Side DC-DC Conversion Circuits
- High Side Drive for Small Brushless DC Motors
- Power Management in Portable, Battery Powered Products

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(BR)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (mΩ)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	C_{iss} Typ (pF)	Package Type
NTHD3101FT1G	0.1733	Pb-free Halide free	Active	P-Channel	with Schottky Diode	-20	8	1.5	3.2	1.1	85	64	-	8.6	7.4	680	Chip FET-8

For more information please contact your local sales support at www.onsemi.com.

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